

PCT

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
Takako YAMAGUCHI et al.	: Examiner: Unassigned): Group Art Unit: Unassigned
Application No.: 10/529,891)
Entry into U.S. National Stage Under 35 U.S.C. § 371: April 1, 2005	·
For: EXPOSURE MASK, METHOD OF DESIGNING AND MANUFACTURING THE SAME, EXPOSURE METHOD AND APPARATUS, PATTERN FORMING METHOD, AND DEVICE MANUFACTURING METHOD	May 3, 2005 :) :) :

Mail Stop Amendment Commissioner for Patents P.O. Box 1450

Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed PTO-1449 form. Copies of the Japanese patent documents (with English language abstracts) and PCT publication are also enclosed.

U.S. Patent No. 6,171,730 is discussed on pages 2-3 of the specification.

Japanese patent document number 11-317345 and U.S. Patent No. 6,497,996 are discussed on page 3 of the subject specification. U.S. Patent No. 6,671,034 and U.S. Patent Application Publication No. 2004/0090610 A1 are English language counterparts of the '345 Japanese patent document.

U.S. Patent No. 6,171,730 B1, U.S. Patent Application Publication No. 2001/046719 A1, International Application No. WO 03/001869 A, McNab et al. "Analytic

study of gratings patterned by evanescent near field optical lithography," Luo et al.

"Surface plasmon resonant interference nanolithography technique," and Alkaisi et al.

"Nanolithography in the Evanescent Near Field" were cited in an International Search

Report, which was mailed on September 27, 2004, from the European Patent Office in

corresponding International Application No. PCT/JP2004/009375. Copies of the

International Search Report and a Written Opinion mailed September 27, 2004 are also

enclosed.

Applicants request that the above information be considered by the Examiner and

that a copy of the enclosed PTO-1449 form be initialed and returned indicating that such

information has been considered.

This Information Disclosure Statement is being filed before the issuance of a first

Office Action on the merits. Therefore, no fee under 37 C.F.R. 1.97(c)(2) is believed due.

Nevertheless, the Commissioner may charge Deposit Account No. 06-1205, should any fee

be due for filing this paper.

Applicants' undersigned attorney may be reached in our Washington D.C. office

by telephone at (202) 530-1010. All correspondence should continue to be directed to our

address given below.

Respectfully submitted,

Attorney for Applicants

David A. Divine

Registration No. 51,275

FITZPATRICK, CELLA, HARPER & SCINTO

30 Rockefeller Plaza

New York, New York 10112-3800

Facsimile: (212) 218-2200

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FORM PTO 1449 (modified)

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U.S. DEPARTMENT OF COMPERCE PATENT AND TRADEMARK OFFICERADEMARK

LIST OF REFERENCES CITED BY APPLICANT(S) (Use several sheets if necessary)

ATTY DOCKET NO. 00684.003654

APPLICATION NO. 10/529,891

APPLICANT Takako YAMAGUCHI et al.

May 3, 2005			FILING DATE April 1, 2005		GROUP Unassigned	
		į	J.S. PATENT DOCUMENTS			
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	US 6,171,730 B1	01/09/2001	Kuroda et al.	430	5	
	2001/0046719 A1	11/29/2001	Yamaguchi et al.	438	11	_
	2003/0129545 A1	07/10/2003	Kik et al.	430	313	
	US 6,497,996	12/24/2002	Naya et al.	430	323	
	US 6,671,034 B1	12/30/2003	Hatakeyama et al.	355	67	
	2004/0090610 A1	05/13/2004	Hatakeyama et al.	355	67	
		FOF	REIGN PATENT DOCUMENTS			
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
	11-317345	11/16/1999	Japan			Abstract
	WO 03/001869 A2	01/09/2003	PCT			
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	ОТ	HER DOCUMENT(S)	(Including Author, Title, Date, Pertinent Pages, Etc.)			
	International Searc Application No. PC	h Report mail T/JP2004/093	ed September 27, 2004, issued in o	correspo	onding Inte	rnational
	Written Opinion ma PCT/JP2004/09375.	ailed Septemb	er 27, 2004, issued in International	Applica	ation No.	
	McNab, S. J., et al., lithography," J. Va	"Analytic stu c. Sci. Techno	dy of gratings patterned by evanes ol. B 18(6), Nov/Dec 2000, pp. 2900-	scent ne 2904.	ear field opt	ical
	Luo, Xiangang, et a Applied Physics Le	al., "Surface p etters, Vol. 84,	lasmon resonant interference nand No. 23, June 7, 2004, pp. 4780-478	olithogra 2.	aphy techni	que,"
	Alkaisi, Maan M., e No. 12-13, July 4, 2	<i>t al.</i> , "Nanolith 001, pp. 877-8	ography in the Evanescent Near F 87.	ield," A	dvanced Ma	aterials, 13,
EXAMINER			DATE CONSIDERED			

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.